

BCR25RM-12LB

Triac

Medium Power Use

REJ03G1715-0100

Rev.1.00

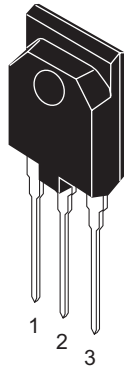
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Features

- $I_{T(RMS)}$: 25 A
- V_{DRM} : 600 V
- I_{FGTI} , I_{RGTI} , I_{RGTHI} : 50 mA
- V_{iso} : 2000 V
- The product guaranteed maximum junction temperature of 150°C
- Insulated Type
- Planar Type

Outline

RENESAS Package code: PRSS0003ZA-A
(Package name: TO-3PFM)



1. T₁ Terminal
2. T₂ Terminal
3. Gate Terminal

Applications

Contactless AC switch, electric heater control, light dimmer, on/off and speed control of small induction motor, on/off control of copier lamp

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Notes: 1. Gate open.

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	25	A	Commercial frequency, sine full wave 360° conduction, $T_c = 96^\circ\text{C}$
Surge on-state current	I_{TSM}	250	A	50 Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusion	I^2t	313	A^2s	Value corresponding to 1 cycle of half wave 50 Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction Temperature	T_j	-40 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-40 to +150	$^\circ\text{C}$	
Mass	—	5.2	g	Typical value
Isolation voltage	V_{iso}	2000	V	$T_a = 25^\circ\text{C}$, AC 1 minute, T_1, T_2 -G terminal to case

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Repetitive peak off-state current	I_{DRM}	—	—	3.0/5.0	mA	$T_j = 125^\circ\text{C} / 150^\circ\text{C}$, V_{DRM} applied	
On-state voltage	V_{TM}	—	—	1.5	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 40\text{ A}$, instantaneous measurement	
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	2.0	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	V_{RGTI}	—	—	2.0	V	
	III	V_{RGTIII}	—	—	2.0	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	50	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	I_{RGTI}	—	—	50	mA	
	III	I_{RGTIII}	—	—	50	mA	
Gate non-trigger voltage	V_{GD}	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C} / 150^\circ\text{C}$, $V_D = 1/2 V_{DRM}$	
Thermal resistance	$R_{th(j-c)}$	—	—	1.7	$^\circ\text{C}/\text{W}$	Junction to case ^{Note3}	
Critical-rate of rise of off-state commutation voltage ^{Note4}	$(dv/dt)_c$	10/1	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C} / 150^\circ\text{C}$	

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is $0.5^\circ\text{C}/\text{W}$.

4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -13\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	